

EVAL\_1K6W\_PSU\_G7\_DD

#### **About this document**

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### Scope and purpose

This document introduces a complete Infineon system solution for a 1600 W server PSU which achieves 80Plus Titanium standard. The <u>EVAL\_1K6W\_PSU\_G7\_DD</u> board is a server power composed of a Continuous Conduction Mode (CCM) bridgeless Power Factor Corrector (PFC) with bi-directional switch and a half-bridge LLC DC-DC resonant converter. This document shows the board using CoolMOS™ MOSFETs and CoolSiC™ Schottky diodes in a top-side cooled SMD package (DDPAK) as well as the specifications and the main results obtained during the test of the 1600 W server PSU.

The Infineon components used in the 1600 W server PSU are:

- 600 V CoolMOS™ G7 superjunction (SJ) MOSFET and 650 V CoolSiC™ G6 Schottky diode
- 40 V OptiMOS™ 6 MOSFET
- 1EDI20N12AF isolated and 2EDN7524F non-isolated gate drivers (EiceDRIVER™)
- XMC1402 and XMC4200 microcontrollers
- ICE2QR2280G CoolSET™ Quasi Resonant (QR) flyback controller

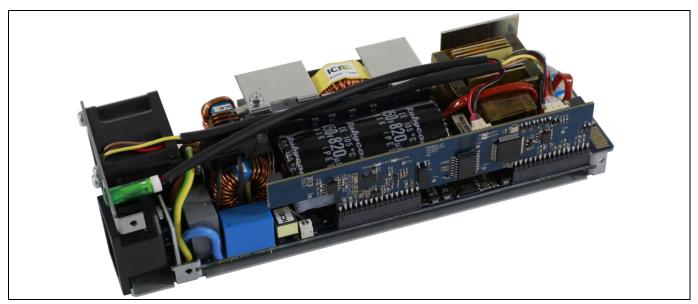


Figure 1 1600 W Titanium server power supply



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**Background and system description** 

# 1 Background and system description

The trend in SMPS in recent years has been toward increased power density with optimized cost. Achieving this higher power density, high efficiency is a key parameter, since heat dissipation must be minimized. The 800 W server PSU developed with Infineon [1], [2] is a good example of the achievable efficiency levels, outperforming 80Plus Platinum efficiency.

However, if higher power is needed with the same form factor, thus increasing the power density, even higher efficiency is required to further reduce the heat dissipation and make the design thermally feasible.

Keeping this in mind, this document introduces a 1600 W server PSU which complies with 80Plus Titanium efficiency, as shown in Figure 2. The 1600 W PSU keeps the same form factor as the previously presented 800 W server PSU. Therefore, the power density is increased to 44 W/in<sup>3</sup> in the design shown.

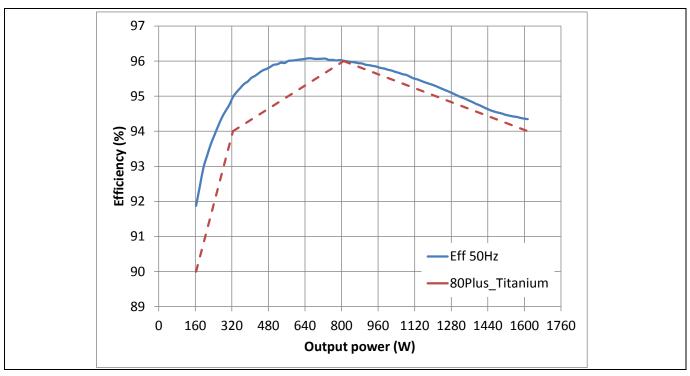


Figure 2 Measured efficiency of the 1600 W server PSU, complying with the Titanium efficiency standard

The efficiency shown can be achieved by using the best-in-class 600 V CoolMOS™ G7 together with 650 V CoolSiC™ G6 Schottky diodes. The outstanding performance of these semiconductor technologies, together with the innovative DDPAK SMD package with top-side cooling, enables a different system thinking, as further presented in [3] and explained in this application note. Due to production variations, efficiency variations in the range of 0.1 percent to 0.2 percent can be seen in the result shown.

The 1600 W server PSU is a system solution (PFC + LLC) developed with Infineon power semiconductors as well as Infineon drivers and microcontrollers. The Infineon devices used in the implementation of the 1600 W server PSU are:

- 150 mΩ 600 V CoolMOS™ G7 (IPDD60R150G7) and 8A 650 V CoolSiC™ G6 Schottky diodes (IDDD08G65C6), all with DDPAK package, for PFC
- 50 mΩ 600 V CoolMOS™ G7 DDPAK package (IPDD60R050G7) and 7 mΩ 40 V OptiMOS™ 6 in Super SO-8 package (BSC007N04LS6) for LLC



### **Background and system description**

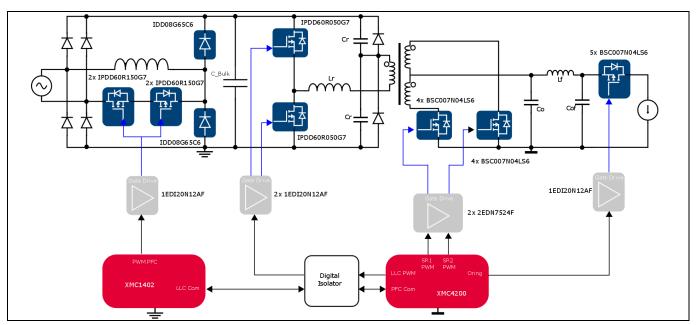
- 0.7 mΩ 40 V OptiMOS<sup>™</sup> 6 in Super SO-8 package (BSC007N04LS6) as O-ring switch
- 1EDI20N12AF isolated and 2EDN7524F non-isolated gate drivers (EiceDRIVER™)
- ICE2QR2280G QR flyback controller with integrated 800 V CoolMOS™ for the bias auxiliary supply
- XMC1402 (PFC) and XMC4200 (LLC) microcontrollers for control implementation

This document will describe the system and board of the 1600 W server SMPS, as well as the specifications and main test results. For further information on Infineon semiconductors see the Infineon website, as well as the Infine on evaluation board search, and the different websites for the different implemented components:

- CoolMOS™ power MOSFETs
- OptiMOS™ power MOSFETs
- <u>CoolSiC</u>™ Schottky diodes
- Gate driver ICs
- QR CoolSET™
- XMC<sup>™</sup> microcontrollers

#### 1.1 System description

The EVAL\_1K6W\_PSU\_G7\_DD design consists of a bridgeless PFC with bi-directional switch [4] as the AC-DC stage and a half-bridge LLC with Synchronous Rectification (SR) as the DC-DC stage (Figure 3). The power supply has been designed to comply with the requirements of a data center server operation.



1600 W Titanium server PSU (EVAL\_1K6W\_PSU\_G7\_DD) - simplified diagram showing the Figure 3 topologies implemented and the Infineon semiconductors used

The PFC stage is operated exclusively at high-line (176 Vrms minimum, 230 Vrms nominal) in CCM with a 65 kHz switching frequency. The bulk capacitance is designed to comply with the hold-up time shown in Table 1. The PFC function to achieve bulk voltage control at an adequate level for the DC-DC converter, while demanding high-quality current from the grid, is implemented in an Infineon XMC1402 microcontroller. Further detail on PFC control implementation in the XMC™ 1000 family can be found in the application notes of other Infineon PSU and PFC evaluation boards [1], [2], [5], [6].



### **Background and system description**

The DC-DC stage is an LLC resonant topology with center-tapped transformer and SR. The resonant frequency of the implemented resonant tank is 160 kHz and the operating switching frequency is allowed to move in the range from 52 kHz to 300 kHz. The targeted output voltage is 12.2 V with a nominal ouput current of 132 A. The LLC control is implemented in an XMC4200 Infineon microcontroller, which includes voltage regulaton, burst mode operation, output Over Current Protection (OCP) and Over Voltage Protection (OVP) and timer configuration for CoolMOS™ and OptiMOS™ safe operation. Further detail about digital control implementation of LLC in the XMC<sup>™</sup> 4000 family can be found in [1], [2], [7].

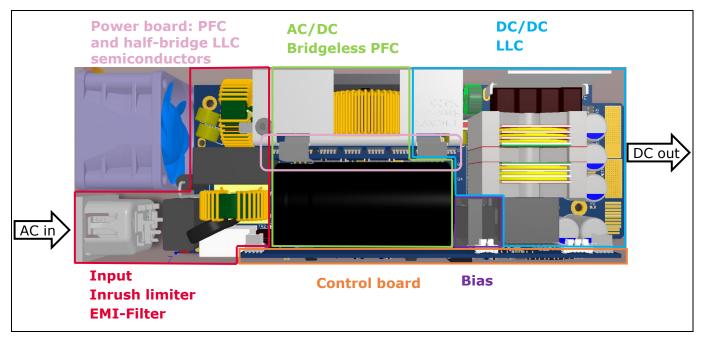
O-ring switches are mounted for efficiency consideration of the full system solution. However, no advance Oring function is included in the control implementation. Furthermore, an I<sup>2</sup>C channel is reserved in the secondary controller, which enables PM-Bus communication.

#### 1.2 **Board description**

Figure 4 shows a placement of the different sections of the EVAL\_1K6W\_PSU\_G7\_DD server PSU with Infineon DDPAK semiconductors. The board shown is 19.3 cm long, with a width of 7 cm and a height of 4.4 cm.

Inmediately after the AC input connector, the fuse and the NTC inrush current limiter are placed together with the input relay, and these are followed by a two-stage EMI filter. In the middle part of the board, the AC-DC stage is placed, including the bulk capacitor. Finally, the DC-DC converter, the O-ring switches and the output connector are placed on the right. In addition, the bias converter generates the required supplies for the driving and control circuitry. The control board is placed along the side of the power supply.

In addition a host board to be connected to the output connector is attached. This board includes power connectors and a sensing point for the output voltage as well as a switch for remote on-off. Furthermore, it offers the possibility of externally supplying the fan, as explained in [1].



Placement of the different sections in the 1600 W PSU with Infineon DDPAK CoolMOS™ Figure 4 and CoolSiC™



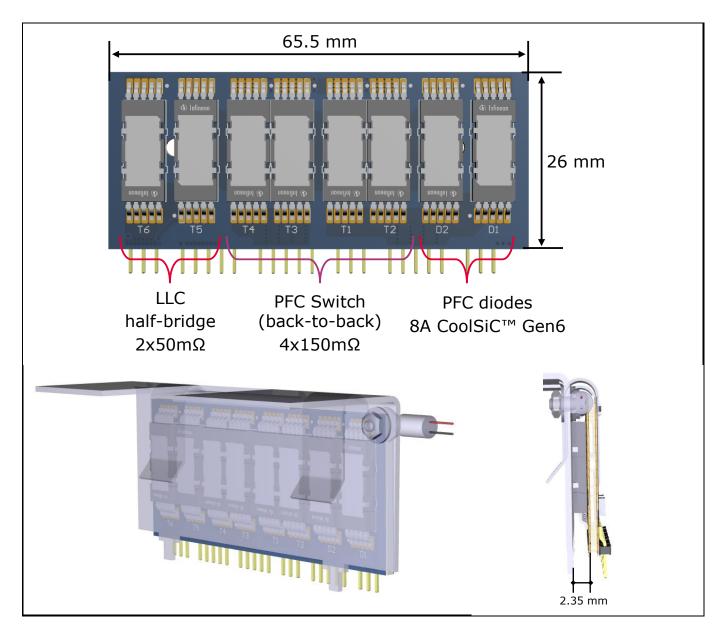
**Background and system description** 

#### 1.3 **DDPAK** power board

The use of the top-side cooled DDPAK package enables different system thinking and the inclusion of SMD packages in high-power SMPS applications [3]. The previously shown placement of the 1600 W PSU is a good example of this system thinking and SMD integration.

The use of CoolMOS™ G7 transistors in both PFC and LLC allows loss reduction due to an E<sub>oss</sub> and R<sub>DS(on)</sub> reduction [3]. Furthermore, the forward voltage in the CoolSiC™ G6 diode is reduced, contributing to lower diode losses [3]. The lower losses together with an improved thermal resistance, which compensates the lower dissipation area in respect to leaded packages, and the low profile of the top-side cooled SMD package, enable mounting of the PFC and half-bridge switches to share the same heatsink.

The use of a power board (Figure 5) enables a high power density design, while having optimized commutation loops and, therefore, low parasitic inductances. This power board, which mounts the PFC CoolMOS™ G7 switches and CoolSiC™ G6 Schottky diodes, together with the LLC CoolMOS™ G7 half-bridge switches, is vertically placed in the central part of the PSU in front of the fan (the pink area in Figure 4). In this case, eight parts are soldered to the power board and share the same heatsink, which is attached by using pressure clips as shown in Figure 5.





Background and system description

Figure 5 Power board mounting the Infineon DDPAK semiconductors for the PFC and half-bridge LLC



Specification and test results

#### 2 **Specification and test results**

This chapter presents the specifications, performance and behavior of the 1600 W server PSU developed using CoolMOS™ G7 in a DDPAK package. Table 1 shows the demonstrator performance and specifications under several steady-state and dynamic conditions.

Summary of specifications and test conditions for the 1600 W PSU Table 1

1 apte 1	Summary	or specifications and test conditions	for the 1600 W PSU		
Test		Conditions	Specification		
Efficiency test		230 Vrms, 50 Hz/60 Hz, 10 percent	80Plus Titanium efficiency.		
		to 100 percent load	$\eta_{pk}$ = 96 percent at 800 W (50 percent load)		
Current THD		230 Vrms, 50 Hz/60 Hz, 10 percent to 100 percent load	THDi less than 10 percent from 20 percent load		
Power factor		230 Vrms, 50 Hz/60 Hz, 10 percent to 100 percent load	PF more than 0.95 from 20 percent load		
Output volta	ge		12.2 V		
Steady-state	V <sub>out</sub> ripple	230 Vrms, 50 Hz/60 Hz, 10 percent to 100 percent load	ΔV <sub>out</sub>   less than 120 mV <sub>pk-pk</sub>		
Inrush currer	nt	230 Vrms, 50 Hz/60 Hz, measured on the first AC cycle	I <sub>in_peak</sub> less than 30 A		
Power line disturbance	AC lost (hold-up time)	230 Vrms, 50 Hz, 10 ms at 100 percent load, 20 ms at 50 percent load	ΔV <sub>out</sub>   less than 240 mV <sub>pk</sub>	No damage: * PSU soft-start if bulk voltage under	
	Voltage sag	200 Vrms, 50Hz/60Hz, different sag conditions, 100 percent load		310 V * PSU soft-start if V AC out of range for certain time	
Brown-out			174 V on; 168 V off		
Load transier	nt	1 A ↔ 66 A, 0.5 A/μs			
		66 A ↔ 133 A, 0.5 A/μs	-  ΔV <sub>out</sub>   less than 240 mV <sub>p</sub>	ok .	
ОСР		30 s at 141 A	LLC off		
		10 s at 149 A	Resume of operation red	quires bulk voltage to	
		1 ms at 168 A	drop under 310 V		
		Output terminals in short-circuit	Detection within switching cycle. Resumption of operation requires bulk voltage to drop under 310 V		
EMI conducte	ed	230 Vrms, 50Hz, full load, resistive load, lab set-up	Complies with Class B li	mits	

#### 2.1 Performance and steady-state waveforms

In this chapter the steady-state waveforms are presented together with the efficiency and the Power Factor (PF) and THD achieved in the 1600 W server PSU presented in this application note. The PSU operates only in high-line (from 176 V to 265 V line voltage) with a nominal input voltage of 230 Vrms. Therefore, the efficiency is presented for this nominal voltage. As shown in Figure 6, the Infineon 1600 W PSU with DDPAK CoolMOS™ G7 and CoolSiC<sup>™</sup> G6 achieves Titanium efficiency.



Specification and test results

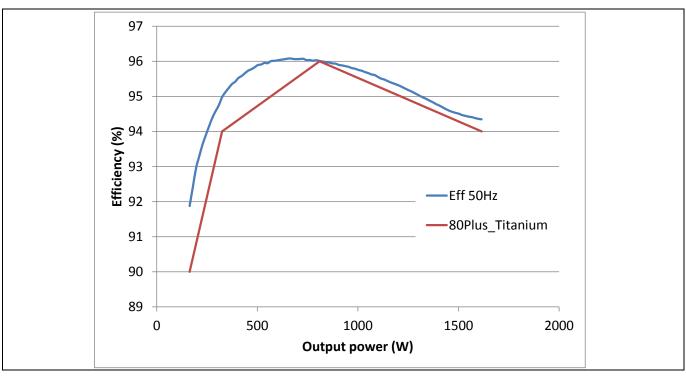


Figure 6 Measured efficiency at 230 V 50 Hz input voltage

Figure 7 depicts the measured PF and THD. The achieved PF is over 0.95 when the output power is higher than the 20 percent of the nominal output power, i.e. 320 W, for both 50 Hz and 60 Hz input voltage. In the case of the THD, the distortion is under 10 percent for output power over the 20 percent level for both 50 Hz and 60 Hz input voltage.

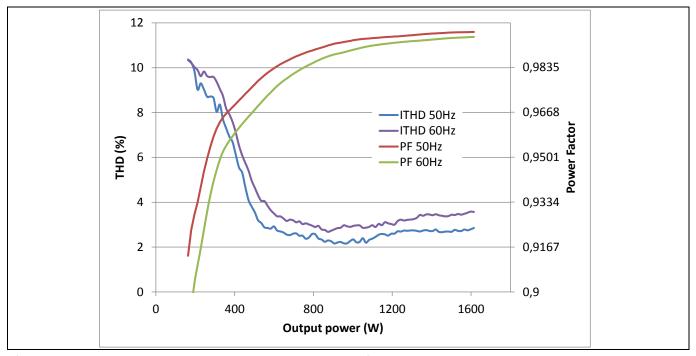


Figure 7 Measured THD and power factor at 230 V input voltage for both 50 Hz and 60 Hz



### Specification and test results

The main waveforms of the PSU are presented for different output power levels for 50 Hz (Figure 8) and 60 Hz (Figure 9) at nominal input voltage. As it can be seen, the input current presents low distortion according to the previously presented curve and the output voltage ripple is under the specified ±120 mV range.

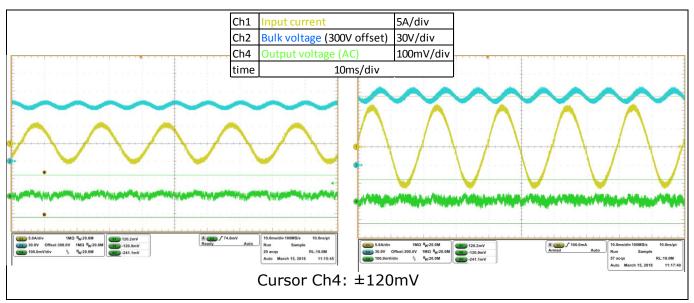


Figure 8 Steady-state waveforms at 230 V 50 Hz for 50 percent load (left) and 100 percent load (right)

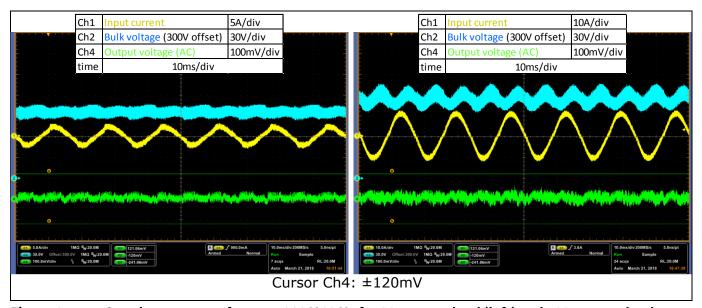


Figure 9 Steady-state waveforms at 230 V 60 Hz for 20 percent load (left) and 100 percent load (right)

### 2.2 Inrush current

In the PSU the inrush current when connecting to the AC source is limited with a NTC. This resistor is short-circuited by a parallel relay before start-up if the input and output voltage conditions to start the PFC are met. The inrush current is measured at the first AC cycle and it is independent on the output load. In Figure 10 the full-load start-up of the server PSU is presented and the inrush current is highlighted. According to the measurement the inrush current is significantly under the specified 30 A in Table 1.



Specification and test results

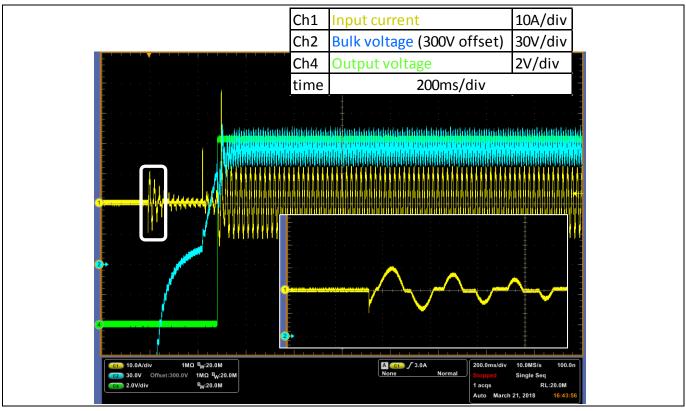


Figure 10 Inrush current of the 1600 W server PSU at full-load start-up

### 2.3 Power line disturbance

Two main line disturbance conditions can occur when connected to the grid. On one side the AC can be lost during a certain time – Line Cycle Drop Out (LCDO) – and, on the other side, the AC voltage can suddenly decrease to an abnormal value – voltage sag. This section introduces the test conditions for both disturbances as well as the SMPS performance when those conditions are applied using a programmable AC source.

### 2.3.1 Line cycle drop-out

The 1600 W power supply operates exclusively in high-line. Therefore the AC LCDO capability is tested from 230 V to 0 V. Different timing, related to the specified hold-up time and the line frequency, is applied as shown in Table 2. The test results (Figure 11 and Figure 12) show that the output voltage is within the specified dynamic variation regardless of the start angle of the voltage drop-out. In case the drop-out is longer than specified, output voltage regulation can be lost, and even a turn-off and restart of the unit is possible if the bulk voltage falls to 310 V.

Table 2 Applied voltage cycles for LCDO test at different loads with 50 Hz AC input voltage

		1 <sup>st</sup> to 10 <sup>th</sup> time (100 ms period)		
Applied voltage	230 V AC	0 V AC	230 V AC	
Timing at different load	50 percent load	20 percent (20 ms)	80 percent (80 ms)	
conditions	100 percent load	10 percent (10 ms)	90 percent (90 ms)	



Specification and test results

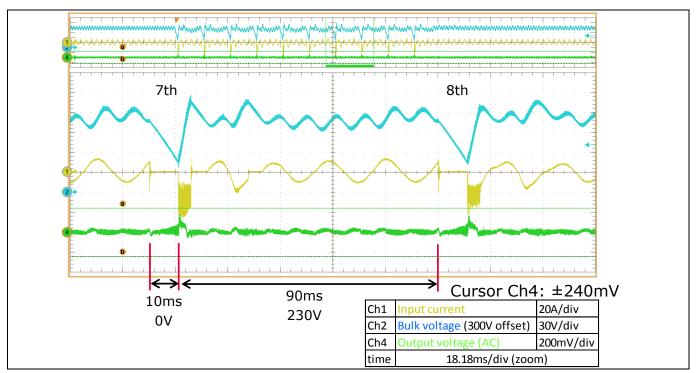


Figure 11 Detail of the 7<sup>th</sup> and 8<sup>th</sup> repetition in a 10 ms LCDO test at 230 V AC, 50 Hz and 100 percent load with a starting angle of 45 degrees

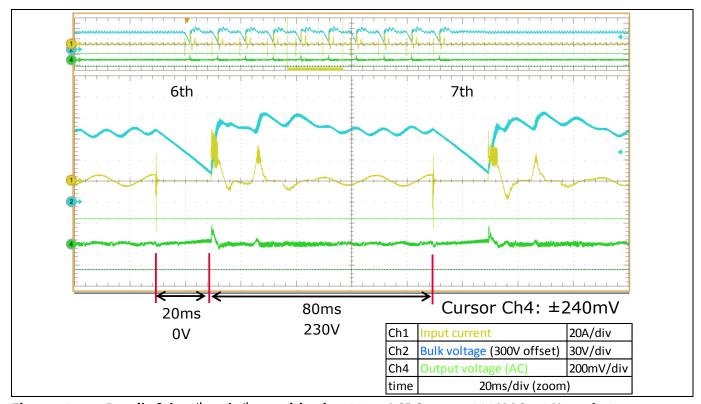


Figure 12 Detail of the 6<sup>th</sup> and 7<sup>th</sup> repetition in a 20 ms LCDO test at 230 V AC, 50 Hz and 50 percent load with a starting angle of 90 degrees



Specification and test results

### 2.3.2 Voltage sag

For high-line, two different voltage sag conditions (Table 3) are considered and tested. Figure 13 shows the PSU behavior with voltage sag according to Table 3. As can be seen, the output voltage is not affected by the input voltage variation. However, if the voltage sag lasts longer than specified in the table, the power supply turns off and restarts with soft-start after an idle time. Figure 14 shows this behavior when a voltage sag to 150 V is applied for longer than 2s.

Table 3 Voltage sag conditions applied in the 1600 W PSU test

		1 <sup>st</sup> to 10 <sup>th</sup> time	
	Steady AC input	Voltage sag (time)	Period
AC input	200 V AC	130 V AC (0.5 s)	5 s
AC input	200 V AC	150 V AC (2 s)	20 s

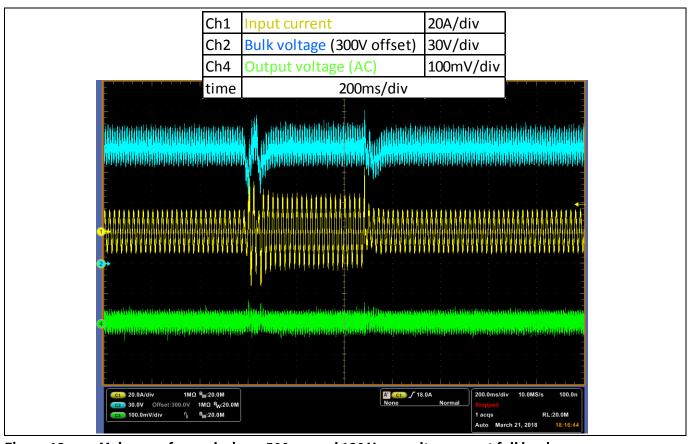


Figure 13 Main waveforms during a 500 ms and 130 Vrms voltage sag at full load



Specification and test results

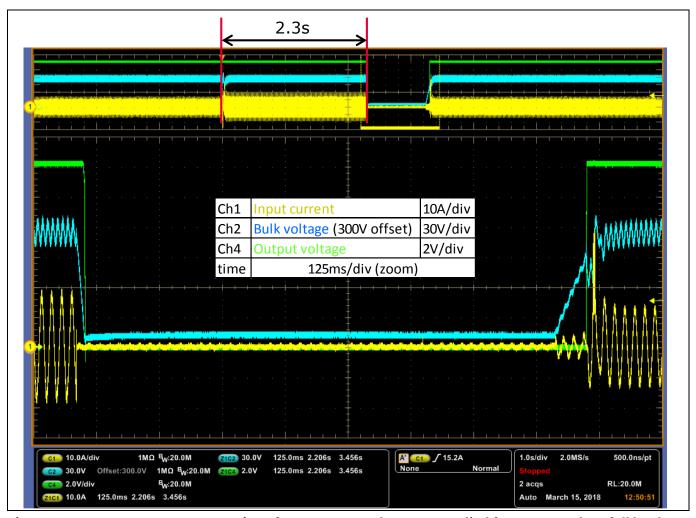


Figure 14 SMPS resumes operation after 150 Vrms voltage sag applied for 3.5 seconds at full load

#### 2.4 **Output voltage dynamic behavior**

In addition to power line disturbance, two other dynamic perturbances can affect the performance of the power supply shown: load and input voltage variation.

#### Load transient response 2.4.1

As specified in Table 1, light-load (1 A) to half-load (66 A) and half-load to full-load (132 A) with 0.5 A/µs steps are considered. Figure 15 and Figure 16 show two examples for the different load steps at different frequency ratios. In all the tested cases the output voltage dynamic ripple is within ±240 mV of the steady-state voltage of 12.2 V.



Specification and test results

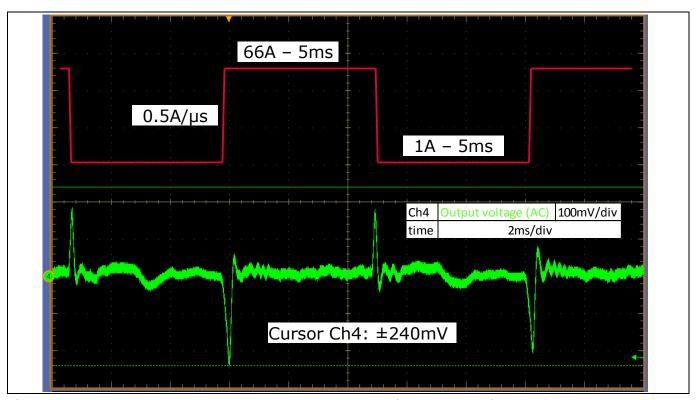


Figure 15 Output voltage response to 1 A to 66 A dynamic load steps with 0.5 A/µs current slope every 5 ms

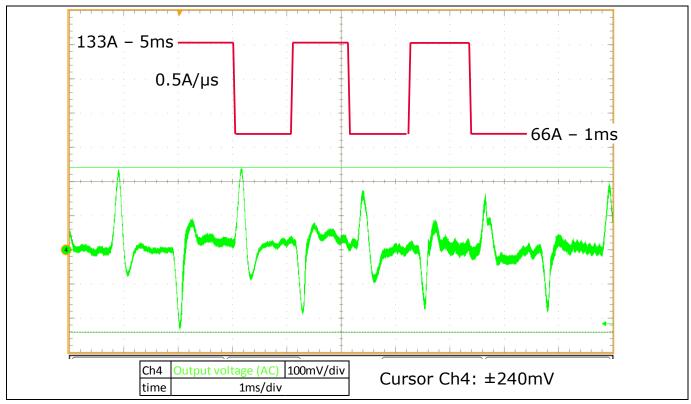


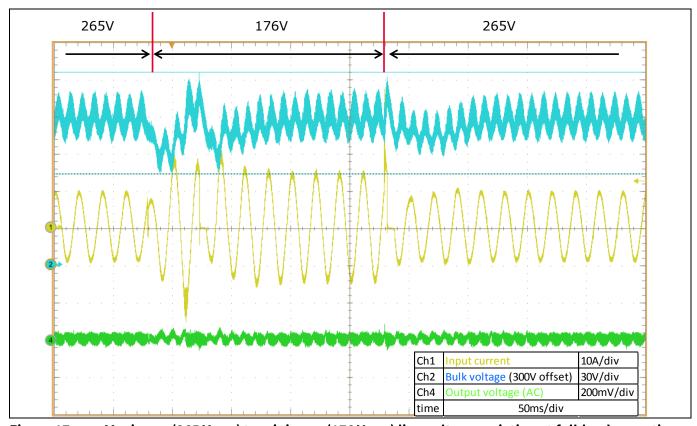
Figure 16 Output voltage response to 132 A to 66 A dynamic load steps with 0.5 A/µs current slope every 1 ms



Specification and test results

#### Input voltage variation 2.4.2

Input voltage variations, as seen in the power line disturbance section, modify the bulk voltage and ultimately affect the output voltage ripple. This can occur as well when the input voltage varies even within the normal operation range, as shown in Figure 17.



Maximum (265 Vrms) to minimum (176 Vrms) line voltage variation at full-load operation Figure 17

#### 2.4.3 **Burst mode**

The DC-DC stage of the 1600 W PSU goes into burst mode operation in light- or no-load conditions, and in those dynamic conditions where the output voltage regulation is lost due to maximum frequency limitation (300 kHz). Figure 18 shows the output voltage ripple for no-load operation of the PSU when the LLC converter is in burst mode.



Specification and test results

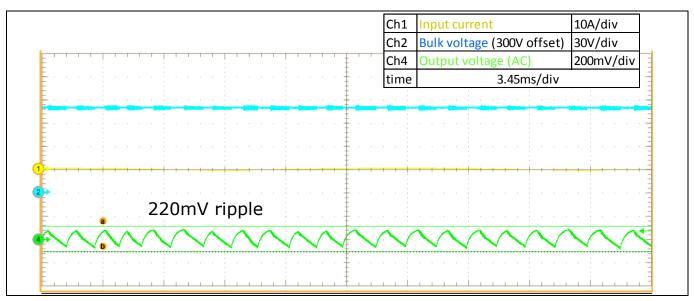


Figure 18 Output voltage ripple in burst mode at no-load operation

### 2.5 Protections

Both stages in the 1600 W server PSU implement protections to ensure robust and reliable operation.

In the case of PFC, the brown-out protection considers the possible voltage sag as already introduced. Furthermore, average and peak inductor current limitations are implemented as well bulk voltage monitoring for both under- and over-shoot.

Regarding the LLC, apart from switching frequency limitation (52kHz to 300kHz), two main protections are implemented: over-current and over-voltage.

### 2.5.1 Over Current Protection (OCP)

The programmed OCP levels, together with the maximum allowed time for each level, are introduced in Table 1. Figure 19 shows the unit reaction to a 155 A load current. LLC shuts down and the bulk voltage must go under 310 V to allow a PSU restart.

In addition, a fast short-circuit protection is implemented by comparing the resonant current with a fixed level, set to 56 A. This enables detection of a very heavy over-load within few switching cycles. The power supply can also be restarted when the bulk voltage decreases under 310 V after a short-circuit fault.



Specification and test results

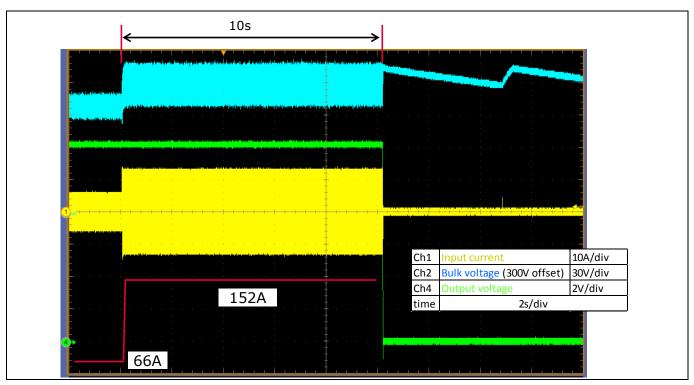


Figure 19 LLC converter of the 1600 W SMPS shut-down due to 155 A OCP

### 2.5.2 Over Voltage Protection (OVP)

In case of control issues in the DC-DC stage of the power supply, OVP is set to 14 V. Figure 20 shows the mentioned protection when the LLC is operated with a modified control loop, which is allowing the output voltage to reach the OVP level.

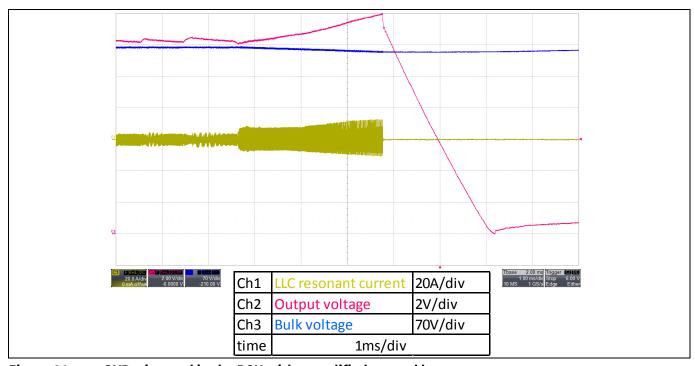


Figure 20 OVP triggered in the PSU with a modified control loop



Specification and test results

### 2.6 Conducted EMI

The high power density 1600 W server PSU with DDPAK includes an EMI filter to comply with the electromagnetic emission standards. In this case the conducted EMI complies with Class B limits as shown in Figure 21. Pure resistive load is used for the conducted EMI test, and the converter runs at nominal output power with nominal (230 V) input voltage at 50 Hz.

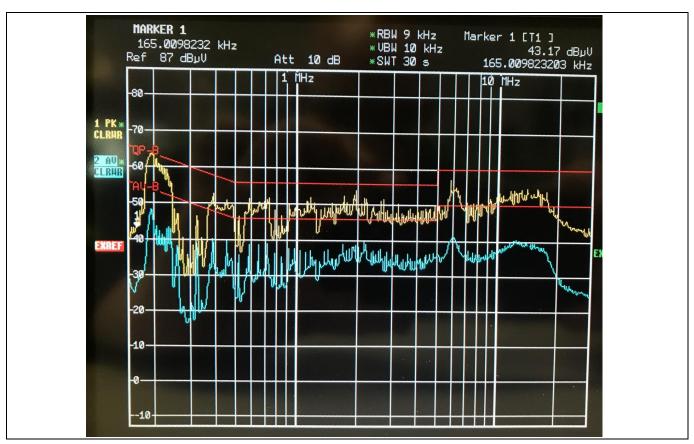


Figure 21 Measured EMI conducted emissions (yellow: quasi-peak, blue: average) at 230 V AC input and 1600 W output resistive load

### 2.7 Thermal measurements

A long time test has been run with attached Type K thermocouplers to the main devices of the EVAL\_1K6W\_PSU\_G7\_DD board. The test has been run for nominal input voltage (230  $V_{rms}$ ) as well as the minimum input voltage (176  $V_{rms}$ ), which is the worst case for the PFC operation. In both cases, nominal load (132 A at 12.2 V output) has been applied during the test at room temperature. The tested unit was enclosed and the fan was controlled by the secondary side controller and supplied from the server power supply output.

Therefore, the results presented in this section provide the thermal performance of the 1600 W server power supply with Infineon semiconductors introduced in this document at room temperature.

The monitored parts in the thermal test are:

- PFC switch: the four switches have been monitored with similar results. The presented measurement corresponds to the hottest device during the test.
- PFC diode: in this case one of the two SiC diodes has been measured.
- PFC choke
- Diode bridge: current flows through part of the input diode bridge during PFC diode conduction.



### Specification and test results

- LLC half-bridge
- LLC transformer
- LLC synchronous rectifiers: the measurement of a sampled device from both SR branches is shown.
- Oring switch: as in the SR case, one of the paralleled devices has been sampled in these measurements.

Figure 22 shows the temperature evolution of the sensed points for nominal input and load conditions. It can be seen that the maximum temperature is obtained in the SR due to the high current in the secondary side. The measured maximum temperature is 84°C at room temperature, which provides margin enough in case the ambient temperature increases.

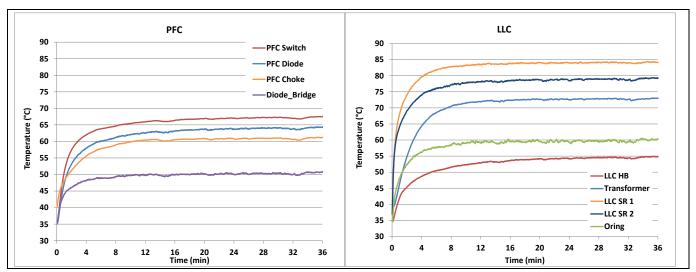


Figure 22 Temperature evolution with operation time in EVAL\_1K6W\_PSU\_G7\_DD at nominal input and load conditions, and room temperature.

In the case of minimum input voltage operation ( $176\,V_{rms}$ ) the thermal behavior is presented in Figure 23. The LLC temperatures are very consistent with the presetend for nominal conditions, since the PFC is regulating the bulk voltage for the DC to DC converter. However, the measured temperatures in the PFC section have increased considerably in respect to the nominal input voltage. This temperature increase is due to the higher input current for the reduced input voltage. Nevertherless, despite the PFC choke is the hot spot of the power supply, together with the SR, the maximum temperature is the same than presented before and there is still margin for higher ambient temperature operation.

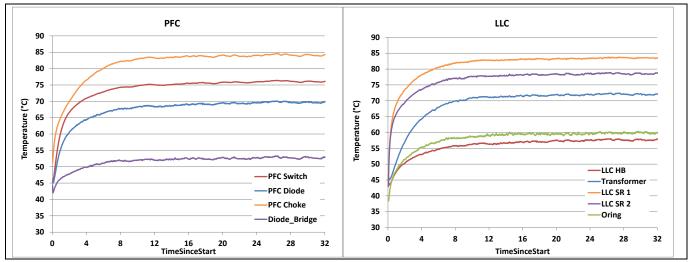


Figure 23 Temperature evolution with operation time in EVAL\_1K6W\_PSU\_G7\_DD at minimum input and nominal load conditions, and room temperature.



**Summary** 

#### 3 **Summary**

This document presents a 1600 W server PSU (EVAL 1K6W PSU G7 DD board) which complies with the 80 Plus Titanium efficiency standard: efficiency is over 96 percent at 50 percent load. The achieved power density is 44 W/in³, which is enabled by the use of SMD packages.

The new DDPAK package is utilized in a power board, which allows reduced commutation loops. Furthermore, the combination of this package with CoolMOS™ G7 and CoolSiC™ G6 diode technologies enables mounting all the semiconductors in the same heatsink and obtains a high power density. In addition, the use of the power board approach will in future enable the testing of new SMD packages, such as QDPAK.

This server PSU also allows the implementation and testing of future Infineon devices and technologies. Further modifications of the power supply shown will be possible by updating different Infineon products such as 2EDF isolated drivers for LLC stage, fifth-generation CoolSET™ in the bias supply or CoolMOS™ S7 as relay replacement. OptiMOS™ 6 information will be available soon. Please check the <u>Infineon website</u> for more information.



Schematics

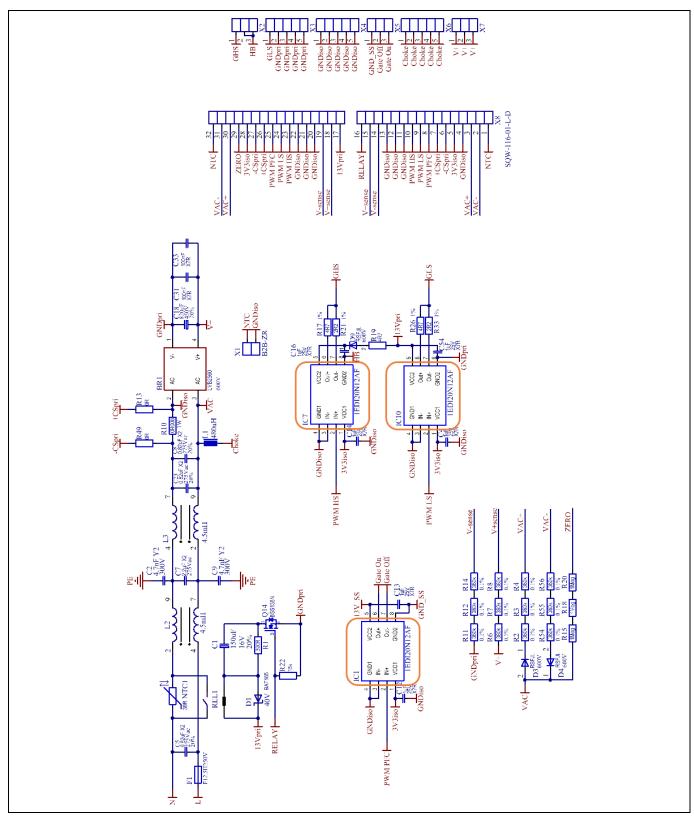


Figure 24 PFC schematic of the 1600 W PSU, which includes the NTC, power board and primary-side control board connectors, as well as the PFC and LLC half-bridge drivers (highlighted in orange). The PFC switch and diode are in the power board.



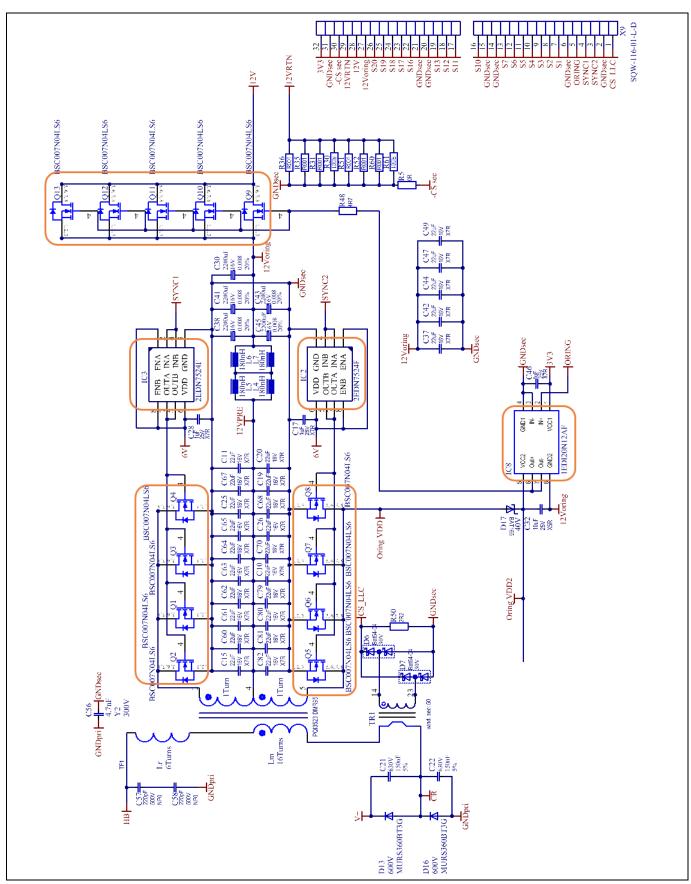


Figure 25 LLC schematic of the 1600 W PSU with the secondary-side control board connector. The primary-side switches and drivers are in the power board and PFC schematic. Infineon products are highlighted in orange.



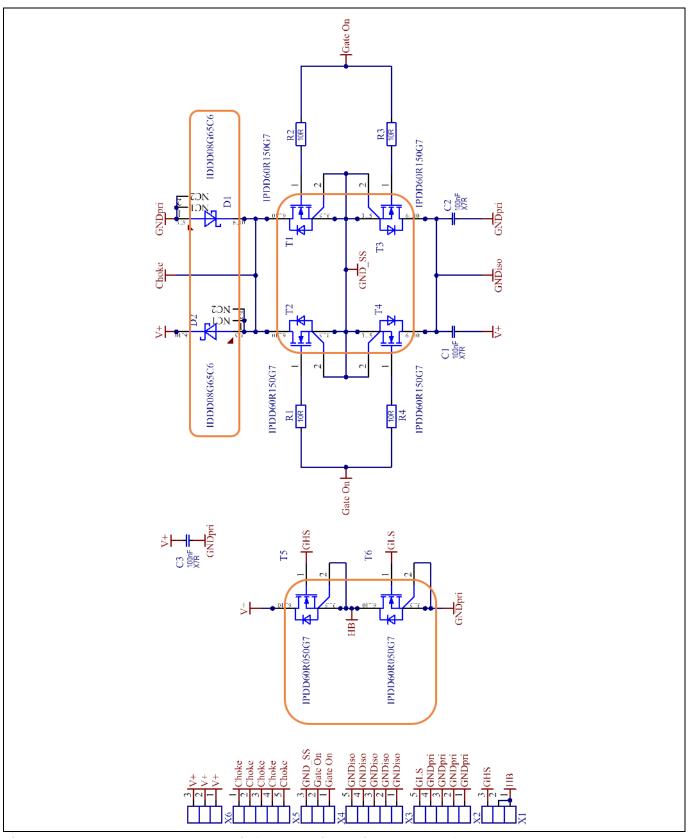


Figure 26 Power board schematic for the main semiconductors of the 1600 W server PSU. The highlighted parts are the Infineon DDPAK MOSFETs and diodes.



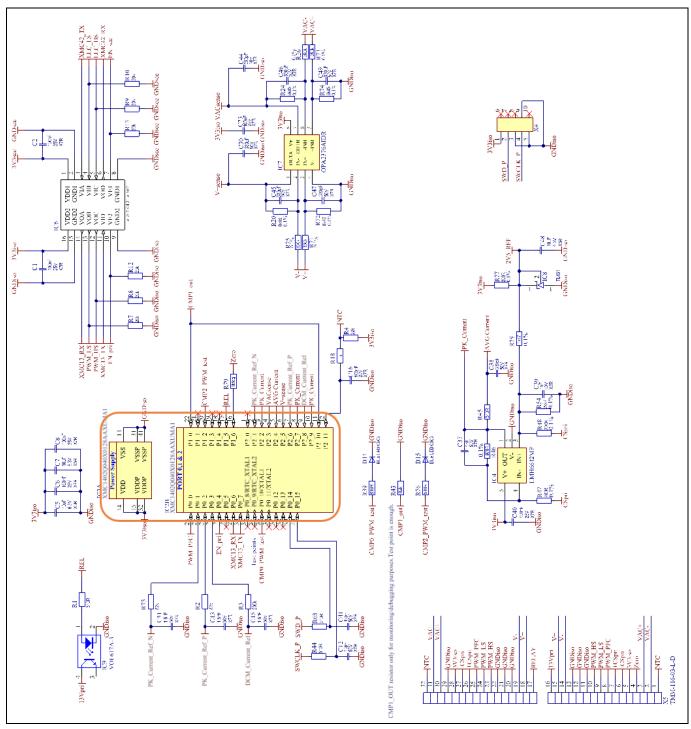


Figure 27 Primary-side controller (XMC1402 highlighted) schematic, including the digital isolator for primary-secondary communication.

# infineon

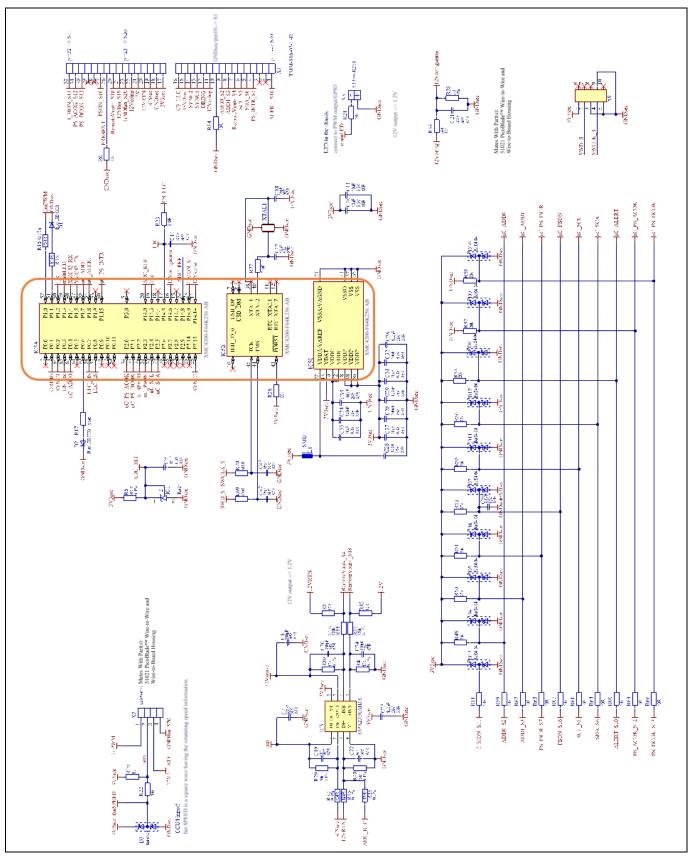


Figure 28 Secondary-side controller (XMC4200 highlighted) schematic, including the signaling for the PSU output connector.



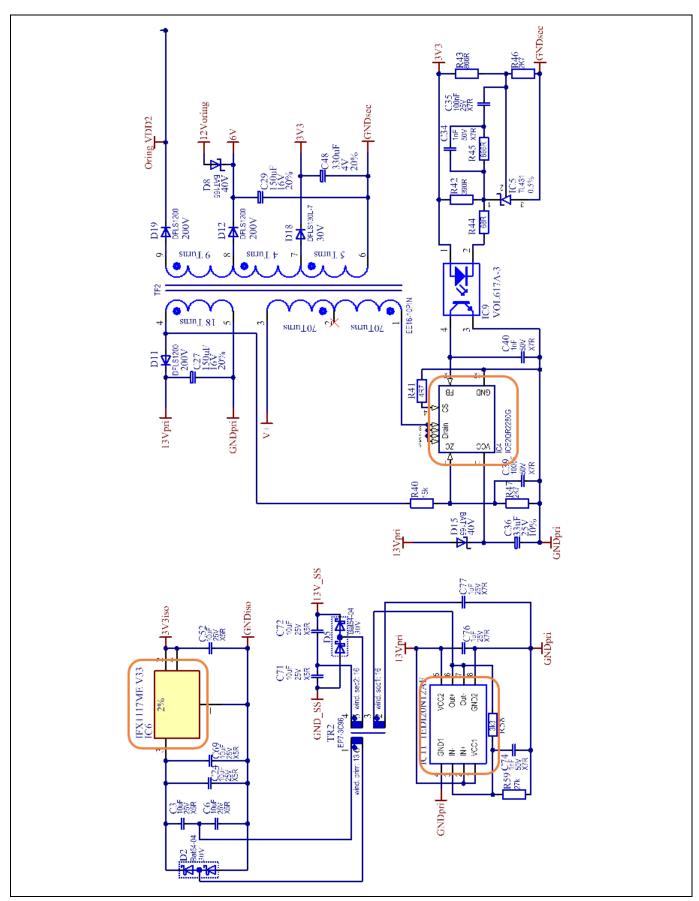


Figure 29 Auxiliary power supply (bias) of the 1600 W server PSU. The implemented Infineon components are highlighted in orange.



Bill of Materials (BoM)

# 5 Bill of Materials (BoM)

Table 4 Main board components

Value	Tolerance	Voltage	Description	Comment
2EDN7524F			Integrated circuit	SMD
1EDI20N12AF			Integrated circuit	SMD
ICE2QR2280G			Integrated circuit	SMD
IFX1117ME V33	2 percent	15 V	Integrated circuit	SMD
30 R	20 percent		NTC resistor	THT
390 R	1 percent		Resistor	SMD
0R008	1 percent		Resistor	SMD
390 R	1 percent		Resistor	SMD
68 R	1 percent		Resistor	SMD
3k3	1 percent		Resistor	SMD
27 k	1 percent		Resistor	SMD
360 k	0.1 percent		Resistor	SMD
15 k	1 percent		Resistor	SMD
866 R	1 percent		Resistor	SMD
2K7	1 percent		Resistor	SMD
1 Meg	1 percent		Resistor	SMD
2R2	1 percent		Resistor	SMD
0 R	1 percent		Resistor	SMD
4R7	1 percent		Resistor	SMD
	·			
R001	1 percent		Resistor	SMD
OJE-SS-112HM		12 V	Relay	THT
BSS138N		60 V	MOSFET	SMD
BSC007N04LS6		40 V	MOSFET	SMD
			Magnetic	THT
•				THT
				THT
				THT
EP7-3C96				THT
4.5 mH				THT
180 nH				SMD
	0.5 percent			SMD
	ore persons			SMD
				THT
		40 V		SMD
			· · · · · · · · · · · · · · · · · · ·	SMD
			·	THT
				SMD
				SMD
			+	SMD
				SMD
		000 V	+	THT
			+	THT
820 μF	20 percent	450 V	Polarized capacitor	THT
	2EDN7524F 1EDI20N12AF ICE2QR2280G IFX1117ME V33 30 R 390 R 0R008 390 R 68 R 3k3 27 k 360 k 15 k 866 R 2K7 1 Meg 2R2 0 R 4R7 R001 OJE-SS-112HM BSS138N  BSC007N04LS6 480 μH PQI3523 DMR95 EE16-10PIN	2EDN7524F           1EDI20N12AF           ICE2QR2280G           IFX1117ME V33         2 percent           390 R         1 percent           0R008         1 percent           390 R         1 percent           68 R         1 percent           3k3         1 percent           27 k         1 percent           360 k         0.1 percent           15 k         1 percent           2K7         1 percent           1 Meg         1 percent           2R2         1 percent           4R7         1 percent           4R7         1 percent           4R01         1 percent           4R0 μH         PQI3523 DMR95           EE16-10PIN         EP7-3C96           4.5 mH         180 nH           TL431         0.5 percent           VOL617A-3         F12.5H250V           BAT165         BAT54-04           LVB2560         DFLS130L-7           MURS360BT3G         DFLS1200           RSFJL         B2B-ZR	Ted   Ted	Integrated circuit   Integrated circuit   IEDI20N12AF   Integrated circuit   Integrated circuit   Integrated circuit   Integrated circuit   IFX1117ME V33   2 percent   SV   Integrated circuit   IFX1117ME V33   2 percent   NTC resistor   390 R   1 percent   Resistor   Resistor   Resistor   390 R   1 percent   Resistor   Resistor   390 R   1 percent   Resistor   Resistor   383   1 percent   Resistor   Resistor   343   1 percent   Resistor   360 k   3 percent   360 k



Bill of Materials (BoM)

1	1	Voltage	Description	Comment
33 μF	10 percent	25 V	Polarized capacitor	SMD
330 μF	20 percent	4 V	Polarized capacitor	SMD
150 μF	20 percent	16 V	Polarized capacitor	SMD
2200 μF	20 percent	16 V	Polarized capacitor	THT
2.2 μF X2	20 percent	275 V AC	Foil capacitor	THT
150 nF	5 percent	630 V	Foil capacitor	THT
0.82 μF X2	20 percent	275 V AC	Foil capacitor	THT
100 nF	X7R	25 V	Ceramic capacitor	SMD
100 pF	X7R	50 V	Ceramic capacitor	SMD
			Ceramic capacitor	
1 μF	X7R	25 V		SMD
100 nF		500 V	Ceramic capacitor	SMD
220 pF	NP0	500 V	Ceramic capacitor	SMD
			Ceramic capacitor	
22 μF	X7R	16 V		SMD
4.7 nF	Y2	300 V	Ceramic capacitor	THT
1 nF	X7R	50 V	Ceramic capacitor	SMD
			Ceramic capacitor	
10 μF	X5R	25 V		SMD
	150 μF 2200 μF 2.2 μF X2 150 nF 0.82 μF X2 100 nF 100 pF 1 μF 100 nF 220 pF 22 μF 4.7 nF 1 nF	150 μF 20 percent 2200 μF 20 percent 2.2 μF X2 20 percent 150 nF 5 percent 0.82 μF X2 20 percent 100 nF X7R 100 pF X7R  1 μF X7R  1 μF X7R  220 pF NPO  22 μF X7R  4.7 nF Y2 1 nF X7R	150 μF 20 percent 16 V 2200 μF 20 percent 16 V 2.2 μF X2 20 percent 275 V AC 150 nF 5 percent 630 V 0.82 μF X2 20 percent 275 V AC 100 nF X7R 25 V 100 pF X7R 50 V  1 μF X7R 25 V 100 nF 500 V 220 pF NPO 500 V  22 μF X7R 16 V 4.7 nF Y2 300 V 1 nF X7R 50 V	150 μF 20 percent 16 V Polarized capacitor 2200 μF 20 percent 16 V Polarized capacitor 2.2 μF X2 20 percent 275 V AC Foil capacitor 150 nF 5 percent 630 V Foil capacitor 0.82 μF X2 20 percent 275 V AC Foil capacitor 100 nF X7R 25 V Ceramic capacitor 100 pF X7R 50 V Ceramic capacitor Ceramic capacitor 1 μF X7R 25 V Ceramic capacitor 220 pF NPO 500 V Ceramic capacitor Ceramic capacitor Ceramic capacitor 1 μF X7R 16 V Ceramic capacitor 1 nF X7R 50 V Ceramic capacitor Ceramic Cerami

### Table 5Power board components

Designator	Value	Tolerance	Voltage	Description	Comment
				600 V CoolMOS™ G7 power	
T5, T6	IPDD60R050G7			transistor, 600 V (VDS)	SMD
				600 V CoolMOS™ G7 power	
T1, T2, T3, T4	IPDD60R150G7			transistor, 600 V (VDS)	SMD
D1, D2	IDDD08G65C6			650 V CoolSiC <sup>™</sup> G6 Schottky diode	SMD
R1, R2, R3, R4	10 R	1 percent		Resistor	SMD
C1, C2, C3	100 nF		500 V	Ceramic capacitor	SMD
	MMT-103-01-L-				
X1, X4, X6	SH			Connector	SMD
	MMT-105-01-L-				
X2, X3, X5	SH			Connector	SMD

### Table 6Control board components

Designator	Value	Tolerance	Voltage	Description	Comment
	XMC1402-				
	Q040X0128AAXUMA				
IC2	1			Integrated circuit	SMD
IC5	XMC4200-F64K256AB			Integrated circuit	SMD
C1, C2, C6, C8, C16, C23,					
C25, C26, C28, C29, C34,	100 nF	X7R	25 V	Ceramic capacitor	SMD



Bill of Materials (BoM)

Designator	Value	Tolerance	Voltage	Description	Comment
C35, C36, C40					
C3, C4, C14, C20, C21, C24,				Ceramic capacitor	
C30, C38, C44, C45, C46,				•	
C47, C49	330 pF	X7R	50 V		SMD
C5, C7, C9, C10, C11, C27,				Ceramic capacitor	
C31, C32, C33, C48	10 μF	X5R	6.3 V		SMD
C12, C17, C18, C41, C42,				Ceramic capacitor	
C43	15 pF	X7R	50 V		SMD
C13, C15, C50, C51	1.5 nF	X7R	50 V	Ceramic capacitor	SMD
C19, C22	4 n7	X7R	50 V	Ceramic capacitor	SMD
C37, C39	1 nF	X7R	50 V	Ceramic capacitor	SMD
D1, D2, D14, D15	Blue LED 0603			LED diode	SMD
D3, D4, D5, D6, D7, D8,					
D9, D10, D11, D12, D13	BAT54-04			Diode	SMD
IC1, IC8	TL431			Integrated circuit	SMD
IC3, IC7	OPA2376AIDR			Integrated circuit	SMD
IC4	LMH6642MF			Integrated circuit	SMD
IC6	ADUM4401ARWZ			Integrated circuit	SMD
IC9	VOL617A-3			Integrated circuit	SMD
	Ferrite bead 60 Ω at			integrated on eart	
L1	100 mHz			Magnetic	SMD
R1, R16, R17, R23, R27,					
R39, R44, R45, R68, R69,					
R70, R76	510 R	1 percent		Resistor	SMD
R2, R34, R43, R75	82 k	1 percent		Resistor	SMD
R3	200 k	1 percent		Resistor	SMD
R4	22 k	1 percent		Resistor	SMD
R5, R47, R48, R77	200 R	0.1 percent		Resistor	SMD
R6, R7, R8, R9, R10, R12,	200 K	0.1 percent		resistor	31112
R13, R28, R49, R50, R51,					
R52, R53, R55, R56, R57,					
R58	20 k	1 percent		Resistor	SMD
R11, R14, R21, R22, R31,		_ per cerre		110010101	
R42, R59, R60, R61, R62,					
R63, R64, R65, R66, R67	10 R	1 percent		Resistor	SMD
R15, R32, R36	124 R	0.1 percent		Resistor	SMD
R18, R19	1 k	1 percent		Resistor	SMD
R20, R24, R72, R74	8k45	0.1 percent		Resistor	SMD
R25, R26, R71, R73	360 k	0.1 percent		Resistor	SMD
R29, R30, R41	10 k	0.1 percent		Resistor	SMD
R33, R37	100 k	0.1 percent		Resistor	SMD
R35	49k9	0.1 percent		Resistor	SMD
R38	9k1	1 percent		Resistor	SMD
R40	12k4	0.1 percent		Resistor	SMD
R46	976 R	0.1 percent		Resistor	SMD
R54	2k87	-			1
	1k47	0.1 percent		Resistor	SMD
R78		0.1 percent		Resistor	SMD
R79	1 Meg	1 percent		Resistor	SMD
X1, X5	TMM-116-03-L-D			Connector	SMD



# Bill of Materials (BoM)

Designator	Value	Tolerance	Voltage	Description	Comment
X2	53398-0471			Connector	SMD
Х3	53398-0271			Connector	SMD
X4, X9				Connector	SMD
XTAL1	12 MHz			Crystal oscillator	SMD



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**Revision history** 

# **Revision history**

### Major changes since the last revision

Page or reference	Description of change
Section 2	Section 2.7 with thermal measurements added.

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